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# ISL9V5045S3ST\_F085

## EcoSPARK® N-Channel Ignition IGBT

500mJ, 450V

### Features

- SCIS Energy = 500mJ at  $T_J = 25^\circ\text{C}$
- Logic Level Gate Drive
- Qualified to AEC Q101
- RoHS Compliant

### Applications

- Automotive Ignition Coil Driver Circuits
- Coil - On Plug Applications

### General Description

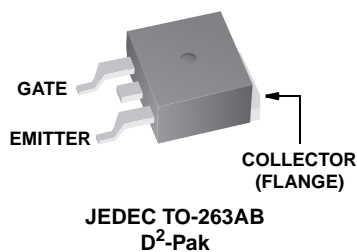
The ISL9V5045S3ST\_F085 is next generation ignition IGBT that offer outstanding SCIS capability in the industry standard D2-Pak (TO-263) plastic package. This device is intended for use in automotive ignition circuits, specifically as a coil drivers. Internal diodes provide voltage clamping without the need for external components.

EcoSPARK® devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

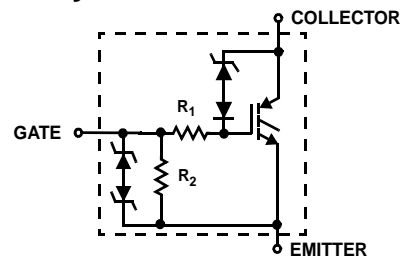


ISL9V5045S3ST\_F085 N-Channel Ignition IGBT

### Package



### Symbol



**Device Maximum Ratings**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Ratings	Units
$BV_{CER}$	Collector to Emitter Breakdown Voltage ( $I_C = 1\text{ mA}$ )	480	V
$BV_{ECS}$	Emitter to Collector Voltage - Reverse Battery Condition ( $I_C = 10\text{ mA}$ )	24	V
$E_{SCIS25}$	At Starting $T_J = 25^\circ\text{C}$ , $I_{SCIS} = 39.2\text{A}$ , $L = 650\ \mu\text{Hy}$	500	mJ
$E_{SCIS150}$	At Starting $T_J = 150^\circ\text{C}$ , $I_{SCIS} = 31.1\text{A}$ , $L = 650\ \mu\text{Hy}$	315	mJ
$I_{C25}$	Collector Current Continuous, At $T_C = 25^\circ\text{C}$ , See Fig 9	51	A
$I_{C110}$	Collector Current Continuous, At $T_C = 110^\circ\text{C}$ , See Fig 9	43	A
$V_{GEM}$	Gate to Emitter Voltage Continuous	$\pm 10$	V
$P_D$	Power Dissipation Total $T_C = 25^\circ\text{C}$	300	W
	Power Dissipation Derating $T_C > 25^\circ\text{C}$	2	W/ $^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-40 to 175	$^\circ\text{C}$
$T_{STG}$	Storage Junction Temperature Range	-40 to 175	$^\circ\text{C}$
$T_L$	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	$^\circ\text{C}$
$T_{pkg}$	Max Lead Temp for Soldering (Package Body for 10s)	260	$^\circ\text{C}$
ESD	Electrostatic Discharge Voltage at 100pF, 1500 $\Omega$	4	kV

**Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
V5045S	ISL9V5045S3ST_F085	TO-263AB	330mm	24mm	800

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off State Characteristics**

$BV_{CER}$	Collector to Emitter Breakdown Voltage	$I_C = 2\text{mA}$ , $V_{GE} = 0$ , $R_G = 1\text{K}\Omega$ , See Fig. 15 $T_J = -40\text{ to }150^\circ\text{C}$	420	450	480	V	
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$I_C = 10\text{mA}$ , $V_{GE} = 0$ , $R_G = 0$ , See Fig. 15 $T_J = -40\text{ to }150^\circ\text{C}$	445	475	505	V	
$BV_{ECS}$	Emitter to Collector Breakdown Voltage	$I_C = -75\text{mA}$ , $V_{GE} = 0\text{V}$ , $T_C = 25^\circ\text{C}$	30	-	-	V	
$BV_{GES}$	Gate to Emitter Breakdown Voltage	$I_{GES} = \pm 2\text{mA}$	$\pm 12$	$\pm 14$	-	V	
$I_{CER}$	Collector to Emitter Leakage Current	$V_{CER} = 320\text{V}$ , $R_G = 1\text{K}\Omega$ , See Fig. 11	$T_C = 25^\circ\text{C}$	-	-	25	$\mu\text{A}$
			$T_C = 150^\circ\text{C}$	-	-	1	mA
$I_{ECS}$	Emitter to Collector Leakage Current	$V_{EC} = 24\text{V}$ , See Fig. 11	$T_C = 25^\circ\text{C}$	-	-	1	mA
			$T_C = 150^\circ\text{C}$	-	-	40	mA
$R_1$	Series Gate Resistance		-	100	-	$\Omega$	
$R_2$	Gate to Emitter Resistance		10K	-	30K	$\Omega$	

**On State Characteristics**

$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_C = 10\text{A}$ , $V_{GE} = 4.0\text{V}$	$T_C = 25^\circ\text{C}$ , See Fig. 4	-	1.25	1.60	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_C = 15\text{A}$ , $V_{GE} = 4.5\text{V}$	$T_C = 150^\circ\text{C}$	-	1.47	1.80	V

### Dynamic Characteristics

$Q_{G(ON)}$	Gate Charge	$I_C = 10A, V_{CE} = 12V, V_{GE} = 5V$ , See Fig. 14	-	32	-	nC	
$V_{GE(TH)}$	Gate to Emitter Threshold Voltage	$I_C = 1.0mA, V_{CE} = V_{GE}$ , See Fig. 10	$T_C = 25^\circ C$	1.3	-	2.2	V
			$T_C = 150^\circ C$	0.75	-	1.8	V
$V_{GEP}$	Gate to Emitter Plateau Voltage	$I_C = 10A, V_{CE} = 12V$	-	3.0	-	V	

### Switching Characteristics

$t_{d(ON)R}$	Current Turn-On Delay Time-Resistive	$V_{CE} = 14V, R_L = 1\Omega, V_{GE} = 5V, R_G = 1K\Omega, T_J = 25^\circ C$ , See Fig. 12	-	0.7	4	$\mu s$
$t_{rR}$	Current Rise Time-Resistive		-	2.1	7	$\mu s$
$t_{d(OFF)L}$	Current Turn-Off Delay Time-Inductive	$V_{CE} = 300V, L = 2mH, V_{GE} = 5V, R_G = 1K\Omega, T_J = 25^\circ C$ , See Fig. 12	-	10.8	15	$\mu s$
$t_{fL}$	Current Fall Time-Inductive		-	2.8	15	$\mu s$
SCIS	Self Clamped Inductive Switching	$T_J = 25^\circ C, L = 650 \mu H, R_G = 1K\Omega, V_{GE} = 5V$ , See Fig. 1 & 2	-	-	500	mJ

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction-Case	TO-263	-	-	0.5	$^\circ C/W$
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### Typical Characteristics

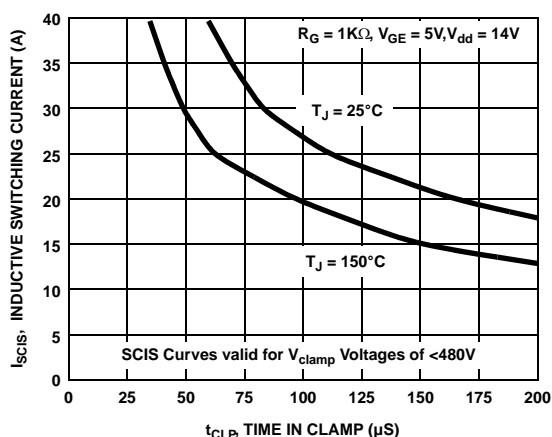


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

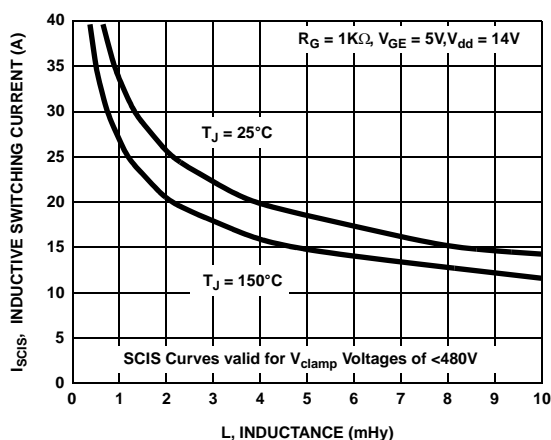
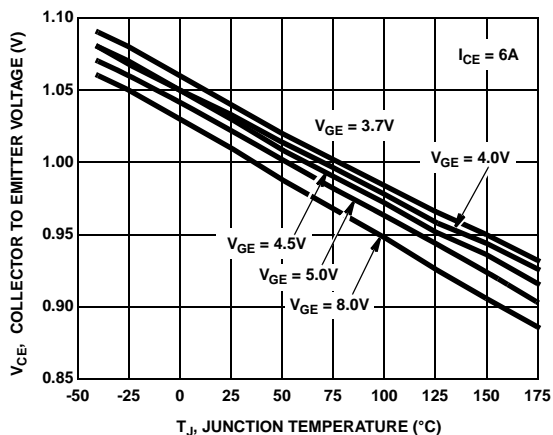
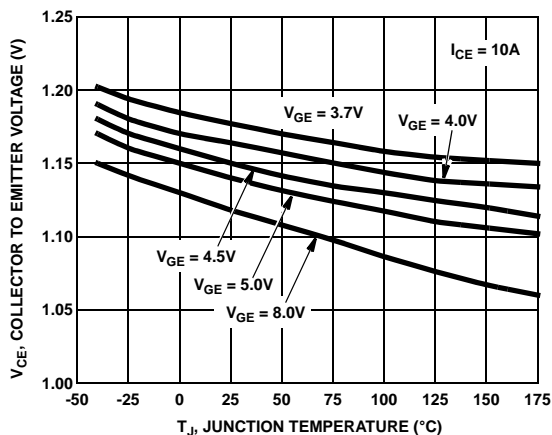


Figure 2. Self Clamped Inductive Switching Current vs Inductance

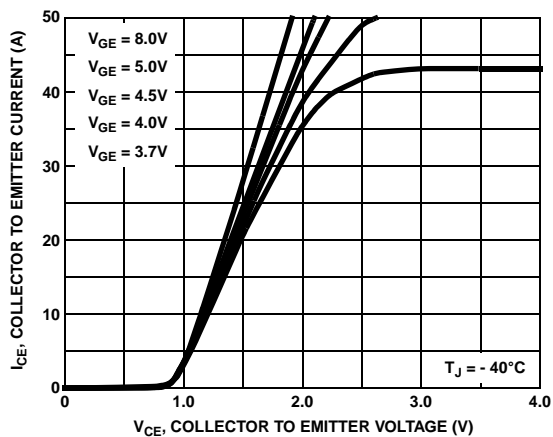
**Typical Characteristics (Continued)**



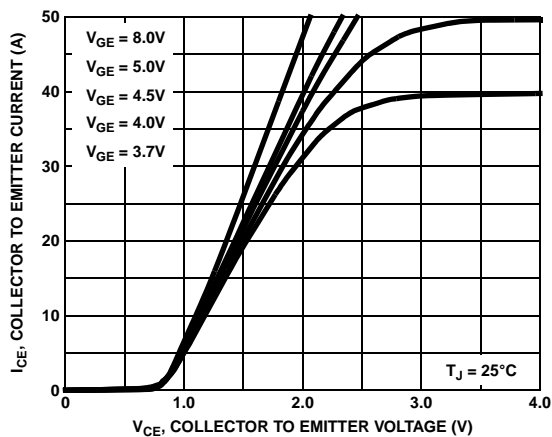
**Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature**



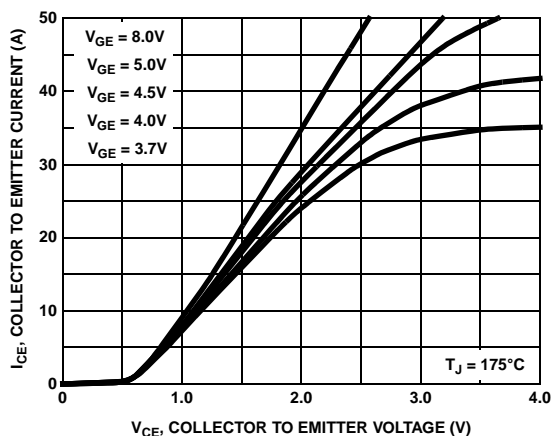
**Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature**



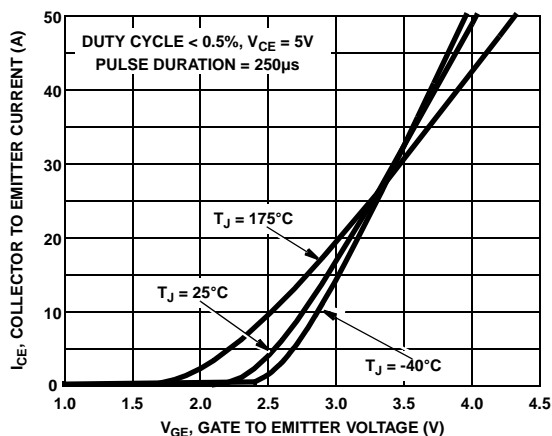
**Figure 5. Collector Current vs Collector to Emitter On-State Voltage**



**Figure 6. Collector Current vs Collector to Emitter On-State Voltage**

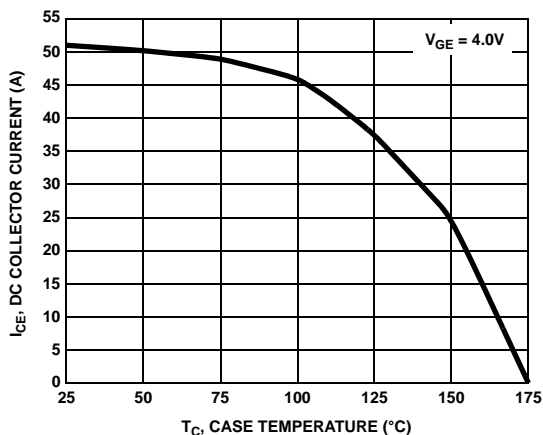


**Figure 7. Collector to Emitter On-State Voltage vs Collector Current**

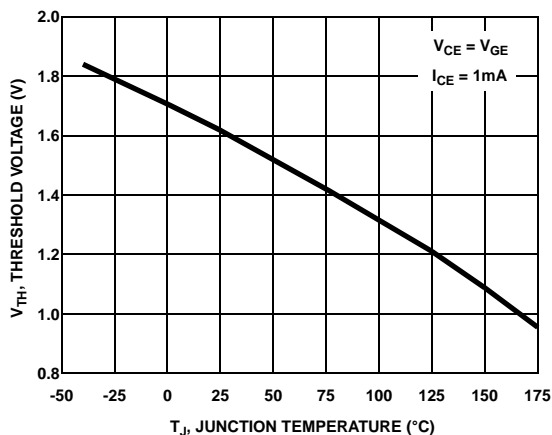


**Figure 8. Transfer Characteristics**

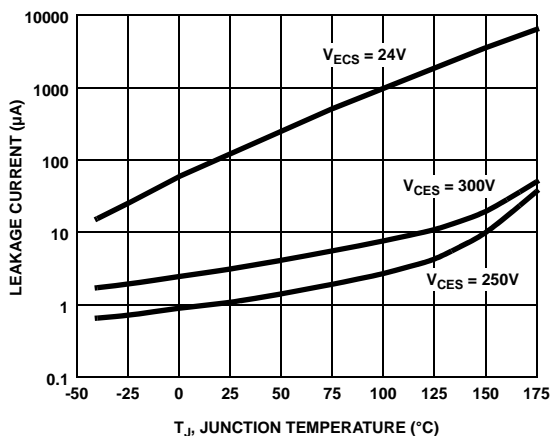
**Typical Characteristics (Continued)**



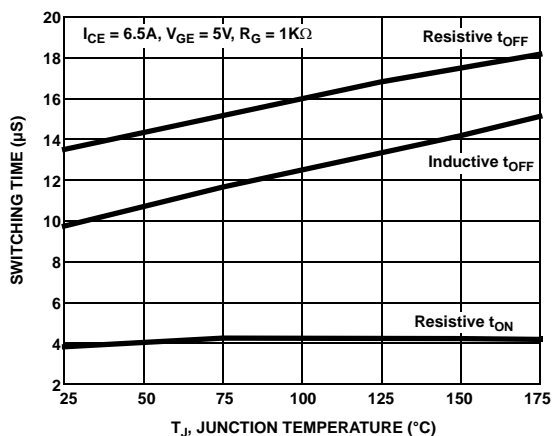
**Figure 9. DC Collector Current vs Case Temperature**



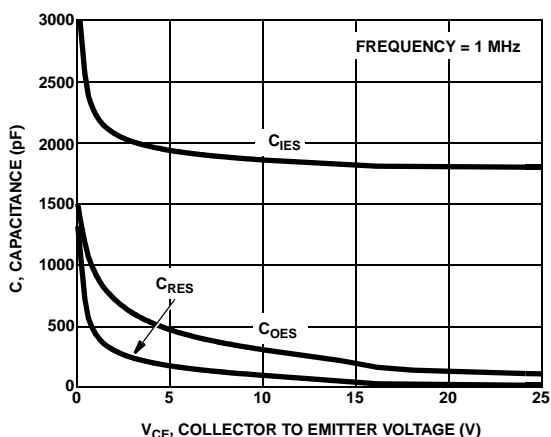
**Figure 10. Threshold Voltage vs Junction Temperature**



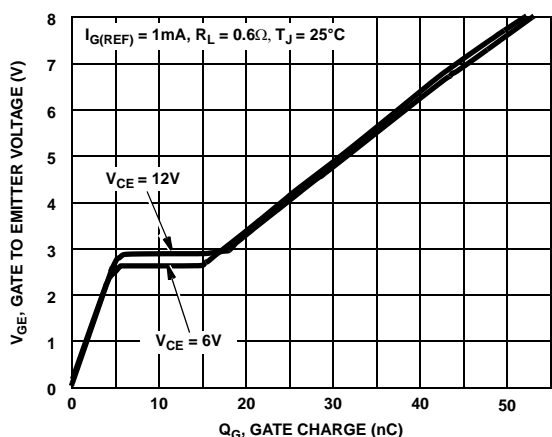
**Figure 11. Leakage Current vs Junction Temperature**



**Figure 12. Switching Time vs Junction Temperature**

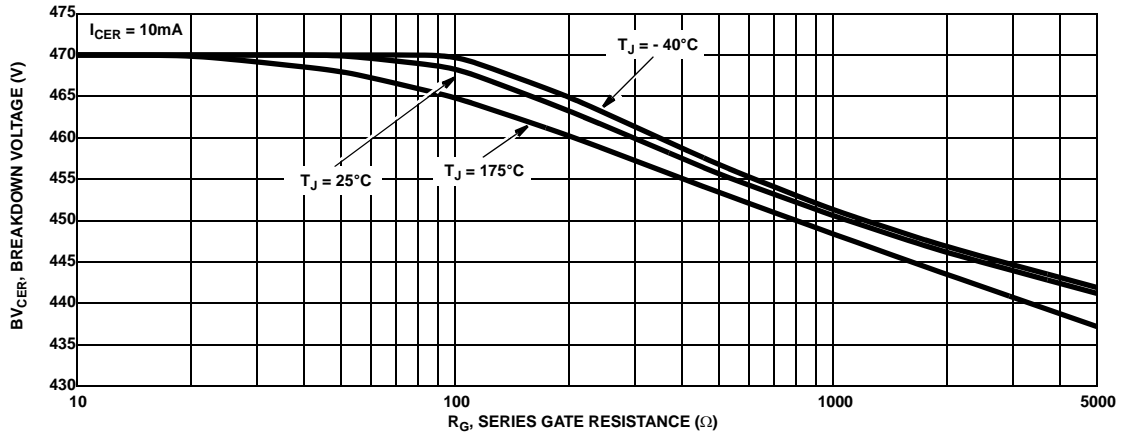


**Figure 13. Capacitance vs Collector to Emitter Voltage**

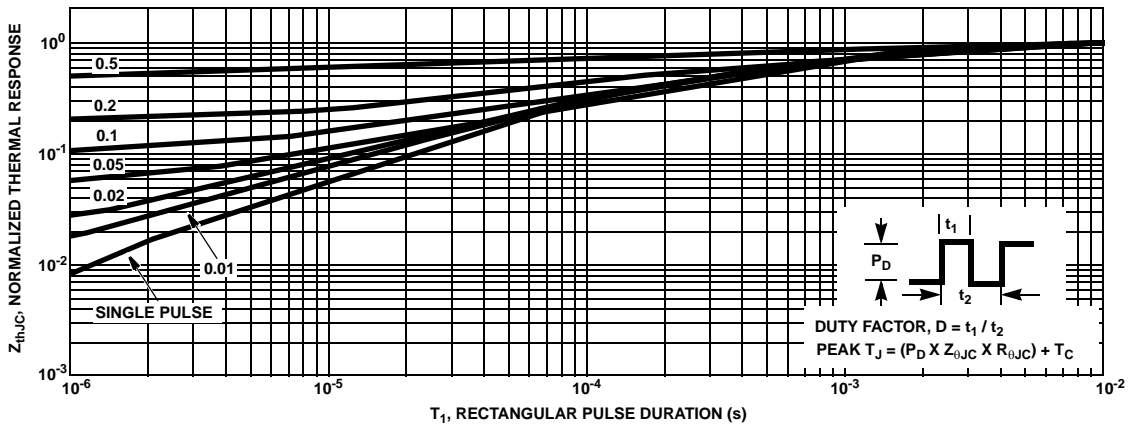


**Figure 14. Gate Charge**

**Typical Characteristics** (Continued)

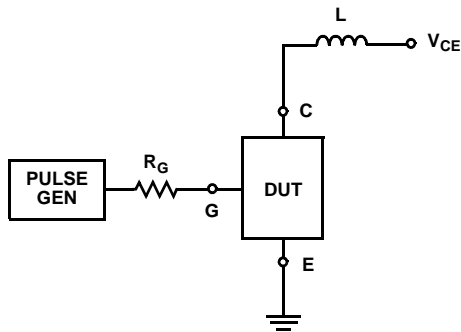


**Figure 15. Breakdown Voltage vs Series Gate Resistance**

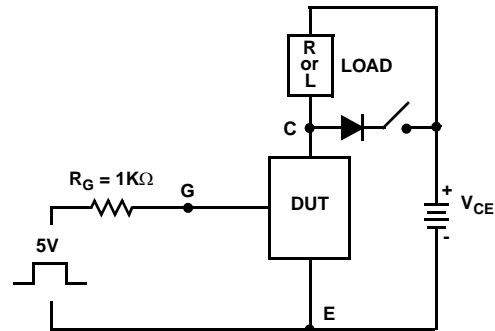


**Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case**

**Test Circuits and Waveforms**

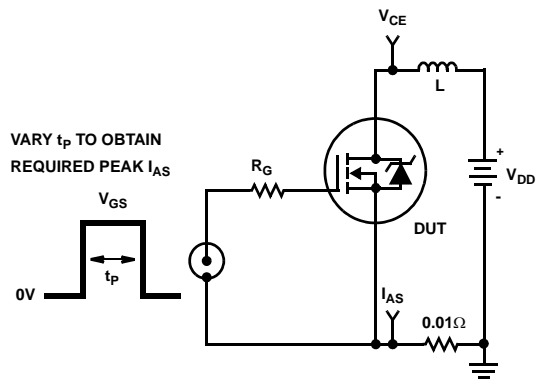


**Figure 17. Inductive Switching Test Circuit**

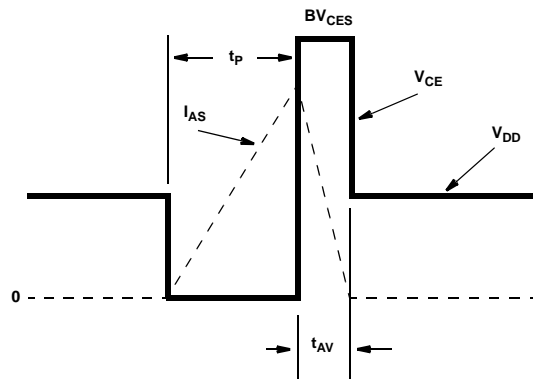


**Figure 18.  $t_{ON}$  and  $t_{OFF}$  Switching Test Circuit**

**Test Circuits and Waveforms** (Continued)



**Figure 19. Energy Test Circuit**



**Figure 20. Energy Waveforms**



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